SGS-THOMSON MICROELECTRONICS

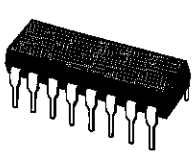
HCC/HCF40100B

32-STAGE STATIC LEFT/RIGHT SHIFT REGISTER

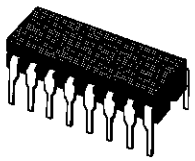
- FULLY STATIC OPERATION
- SHIFT LEFT/SHIFT RIGHT CAPABILITY
- MULTIPLE PACKAGE CASCADING
- RECIRCULATE CAPABILITY
- LIFO OR FIFO CAPABILITY
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

The **HCC40100B** (extended temperature range) and **HCF40100B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF40100B** is a 32-stage shift register containing 32 D-type master-slave flip-flops. The data present at the SHIFT-RIGHT INPUT is transferred into the first register stage synchronously with the positive CLOCK edge, provided the LEFT/RIGHT CONTROL is at a low level, the RECIRCULATE CONTROL is at a high level, and the CLOCK INHIBIT is low. If the LEFT/RIGHT CONTROL is at a high level and the RECIRCULATE CONTROL is also high, data at the SHIFT-LEFT INPUT is transferred into the 32nd register stage synchronously with the positive CLOCK transition, provided the CLOCK INHIBIT is low. The state of the LEFT/RIGHT CONTROL, RECIRCULATE CONTROL, and CLOCK INHIBIT should not be changed when the CLOCK is high. Data is shifted one stage left or one stage right depending on the state of the LEFT/RIGHT CONTROL, synchronously with the positive CLOCK edge. Data clocked into the first or 32nd register states is available at the SHIFT-LEFT or SHIFT-RIGHT OUTPUT respectively, on the next negative CLOCK transition (see Data Transfer Table). No shifting occurs on the positive CLOCK edge if the CLOCK INHIBIT line is at a high level. With the RECIRCULATE CONTROL low, data in the 32nd stage is shifted into the first stage when the LEFT/RIGHT CONTROL is low and from the 1st stage to the 32nd stage when the LEFT/RIGHT CONTROL is high.



EY
(Plastic Package)



F
(Ceramic Frit Seal Package)

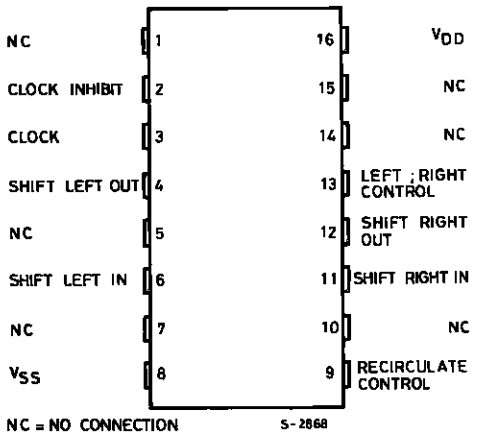
M1
(Micro Package)

C1
(Plastic Chip Carrier)

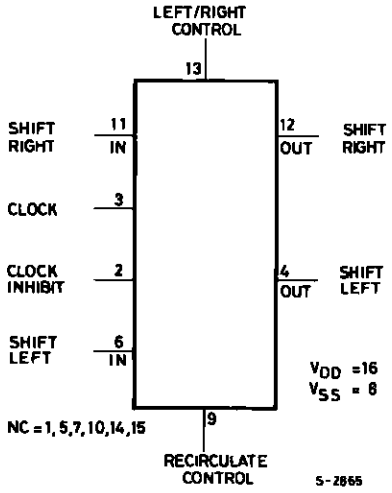
ORDER CODES :

HCC40100BF	HCF40100BM1
HCF40100BEY	HCF40100BC1

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

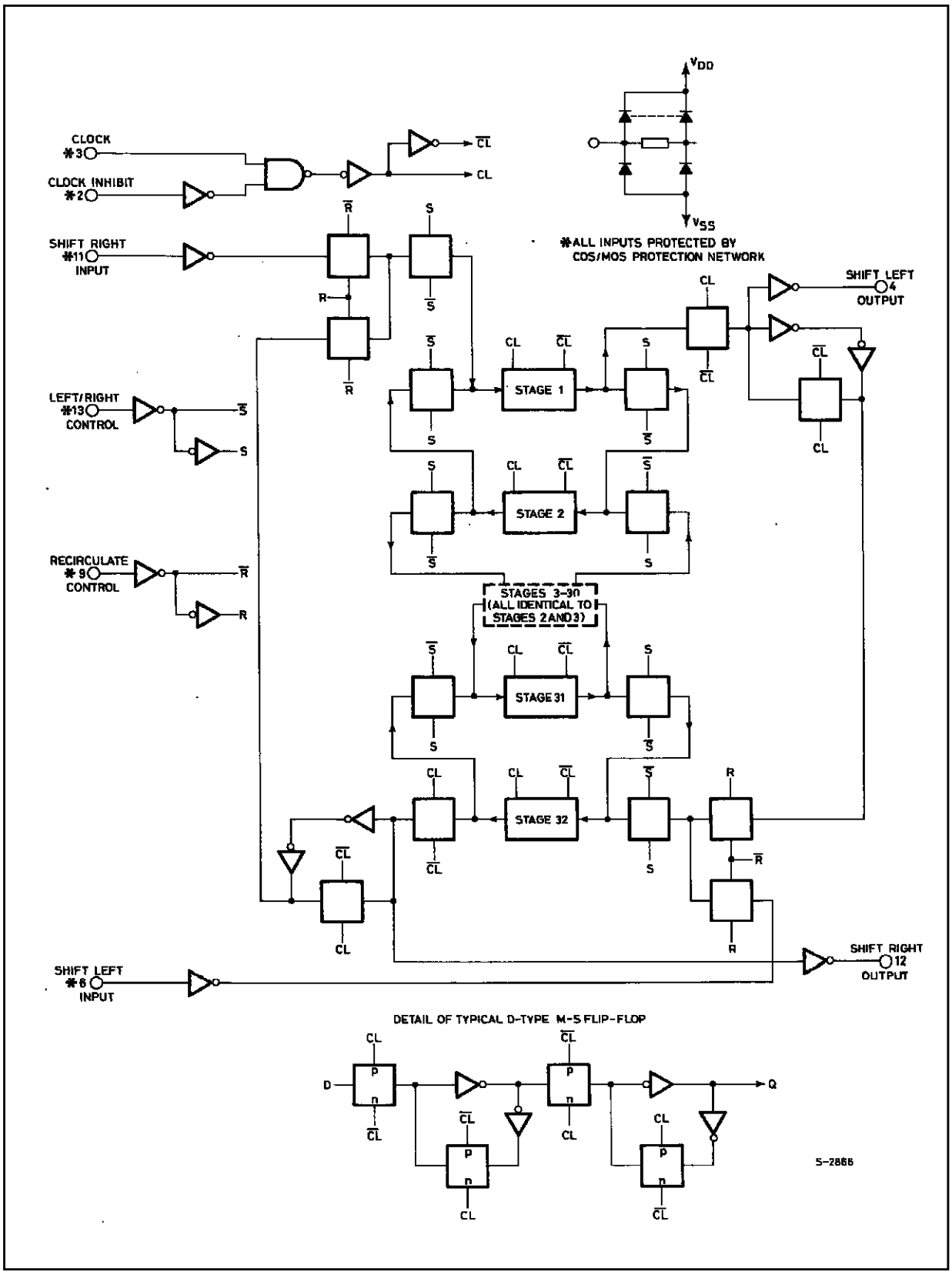
Symbol	Parameter	Value	Unit
V_{DD}*	Supply Voltage : **HCC** Types **HCF** Types	– 0.5 to + 20 – 0.5 to + 18	V V
V_i	Input Voltage	– 0.5 to V_{DD} + 0.5	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature : **HCC** Types **HCF** Types	– 55 to + 125 – 40 to + 85	°C °C
T_{stg}	Storage Temperature	– 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : **HCC** Types **HCF** Types	3 to + 18 3 to + 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : **HCC** Types **HCF** Types	– 55 to + 125 – 40 to + 85	°C °C

LOGIC DIAGRAM



TRUTH TABLES

CONTROL

Left/Right Control	Clock Inhibit	Recirculate Control	Action	Input Bit Origin
1	0	1	Shift Left	Shift Left Input
1	0	0	Shift Left	Stage 1
0	0	1	Shift Right	Shift Right Input
0	0	0	Shift Right	Stage 32
X	1	X	No Shift	–

DATA TRANSFER

Initial State			Clock	Resulting State	
Data Input	Clock Inhibit	Internal Stage	Level Change	Internal Stage Q	Output
0	0	X	_/‾	0	NC
X	0	0	‾_	NC	0
1	0	X	_/‾	1	NC
X	0	1	‾_	NC	1
X	1	1	X	NC	NC

0 = Low level 1 = High level X= Don't Care. NC = No change.

* For Shift-Right Mode
Data Input = SHIFT-RIGHT INPUT (Pin 11)
Internal Stage = Stage 1 (Q1)
Output = SHIFT-LEFT OUTPUT (Pin 4).

For Shift-left Mode
Data input = SHIFT LEFT INPUT (Pin 6)
Internal Stage = Stage 32 (Q32)
Output = SHIFT-RIGHT OUTPUT (Pin 12).

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value							Unit
			V_I (V)	V_O (V)	$\|I_O\|$ (μA)	V_{DD} (V)	T_{Low}*		25°C			T_{High}*		
							Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
I_L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μA
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V_{OH}	Output High Voltage		0/ 5		< 1	5	4.95		4.95			4.95		V
			0/10		< 1	10	9.95		9.95			9.95		
			0/15		< 1	15	14.95		14.95			14.95		
V_{OL}	Output Low Voltage		5/0		< 1	5		0.05			0.05		0.05	V
			10/0		< 1	10		0.05			0.05		0.05	
			15/0		< 1	15		0.05			0.05		0.05	

* T_{Low} = – 55°C for **HCC** device : – 40°C for **HCF** device.
* T_{High} = + 125°C for **HCC** device : + 85°C for **HCF** device.
The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter		Test Conditions				Value							Unit
			V_I (V)	V_O (V)	$\|I_O\|$ (μA)	V_{DD} (V)	T_{Low}*		25°C			T_{High}*		
							Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
V_{IH}	Input High Voltage			0.5/4.5	< 1	5	3.5		3.5			3.5		V
				1/9	< 1	10	7		7			7		
				1.5/13.5	< 1	15	11		11			11		
V_{IL}	Input Low Voltage			4.5/0.5	< 1	5		1.5			1.5		1.5	V
				9/1	< 1	10		3			3		3	
				13.5/1.5	< 1	15		4			4		4	
I_{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	– 2		– 1.6	– 3.2		– 1.15		mA
			0/ 5	4.6		5	– 0.64		– 0.51	– 1		– 0.36		
			0/10	9.5		10	– 1.6		– 1.3	– 2.6		– 0.9		
			0/15	13.5		15	– 4.2		– 3.4	– 6.8		– 2.4		
		HCF Types	0/ 5	2.5		5	– 1.53		– 1.36	– 3.2		– 1.1		
			0/ 5	4.6		5	– 0.52		– 0.44	– 1		– 0.36		
			0/10	9.5		10	– 1.3		– 1.1	– 2.6		– 0.9		
			0/15	13.5		15	– 3.6		– 3.0	– 6.8		– 2.4		
I_{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36		mA
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I_{IH}, I_{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μA
		HCF Types	0/15			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
C_I	Input Capacitance			Any Input						5	7.5			pF

* T_{Low} = – 55°C for **HCC** device : – 40°C for **HCF** device.
* T_{High} = + 125°C for **HCC** device : + 85°C for **HCF** device.
The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

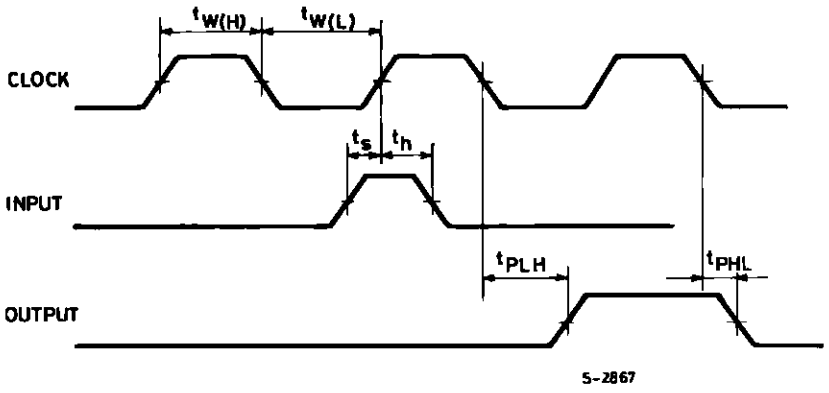
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200kΩ, typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions	Value				Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH}, t_{PHL}	Propagation Delay Time Clock to Shift Left/Right Output		5		360	720	ns
			10		165	330	
			15		115	230	
t_{THL}, t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

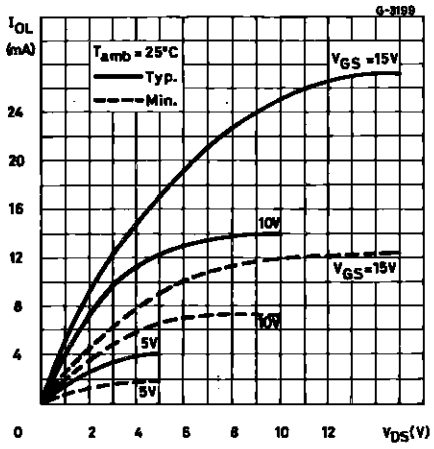
DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{setup}	Data Setup Time		5	100	50		ns
			10	20	10		
			15	10	5		
t_{hold}	Data Hold Time		5	275	170		ns
			10	100	75		
			15	75	50		
t_W	Clock Input Pulse Width Low Level		5	450	225		ns
			10	230	115		
			15	190	95		
t_W	Clock Input Pulse Width High Level		5	280	140		ns
			10	150	75		
			15	140	70		
f_{CL}	Maximum Clock Input Frequency		5	1	2		MHz
			10	2.5	5		
			15	3	6		

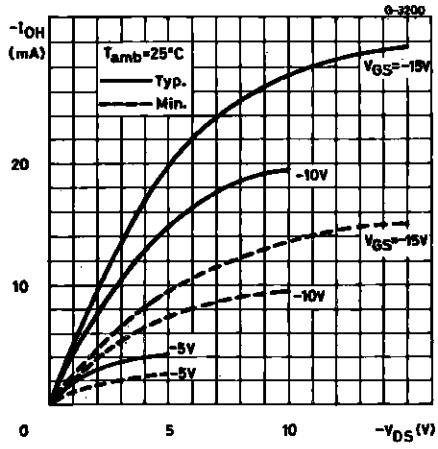
WAVEFORMS



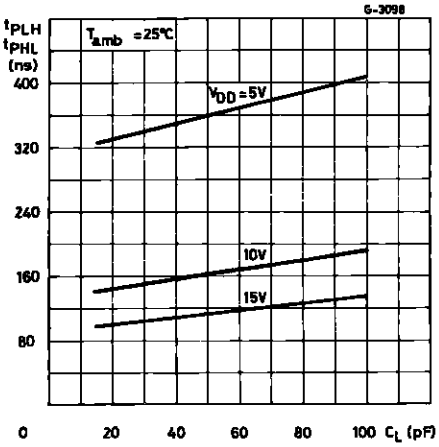
Output Low (sink) Current Characteristics.



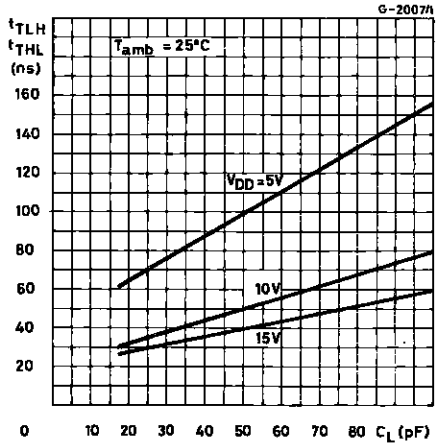
Output High (source) Current Characteristics.



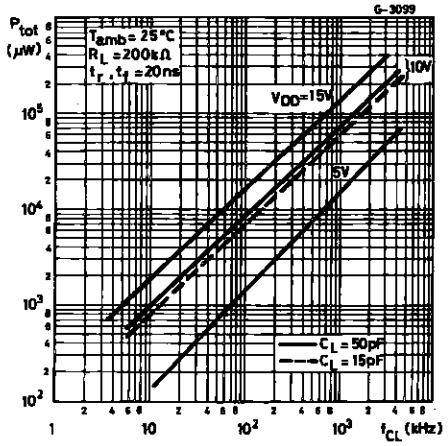
Typical Propagation Delay Time (clock to shift left right) vs. Load Capacitance.



Typical Transition Time vs. Load Capacitance.

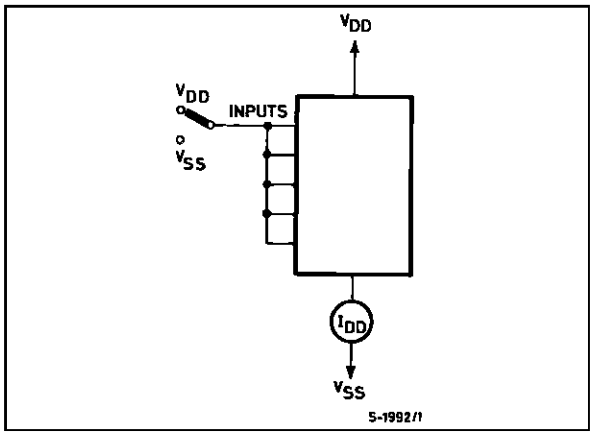


Typical Dynamic Power Dissipation vs. Clock Frequency .

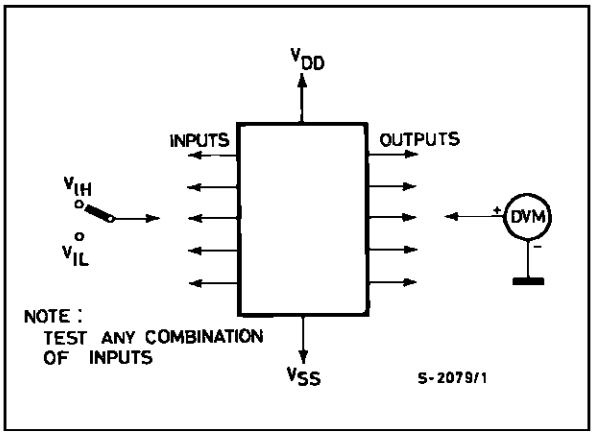


TEST CIRCUITS

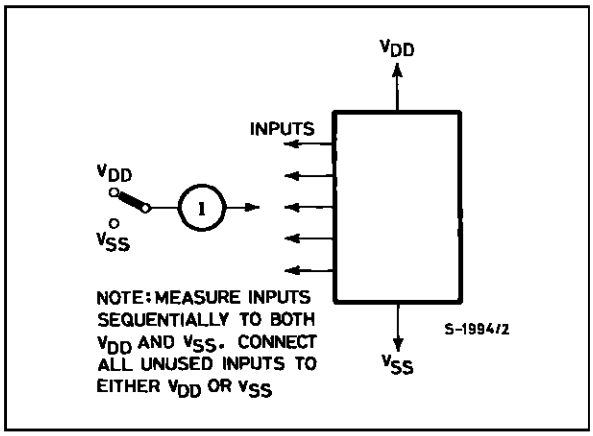
Quiescent Device Current.



Input Voltage.

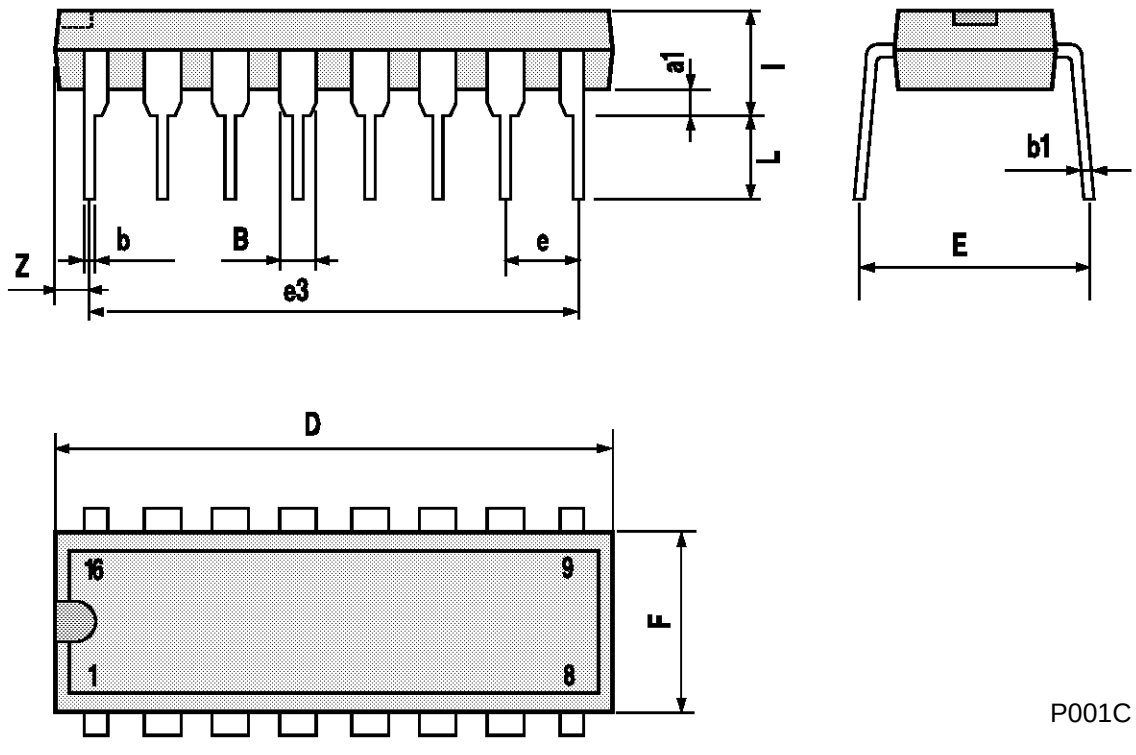


Input Leakage Current.



Plastic DIP16 (0.25) MECHANICAL DATA

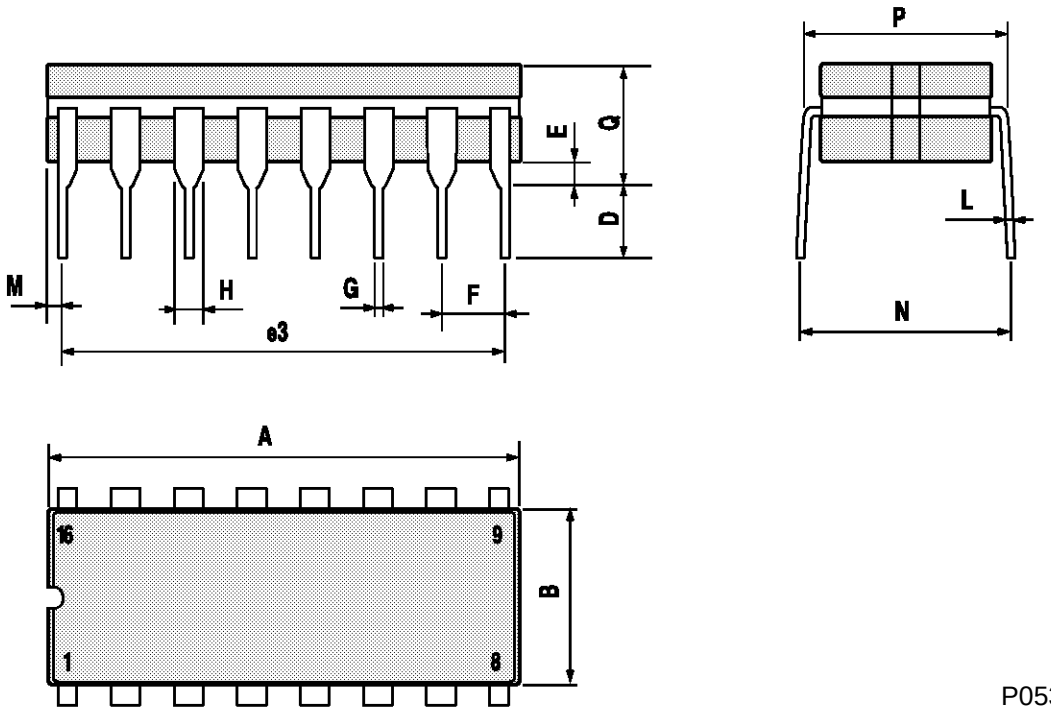
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



P001C

Ceramic DIP16/1 MECHANICAL DATA

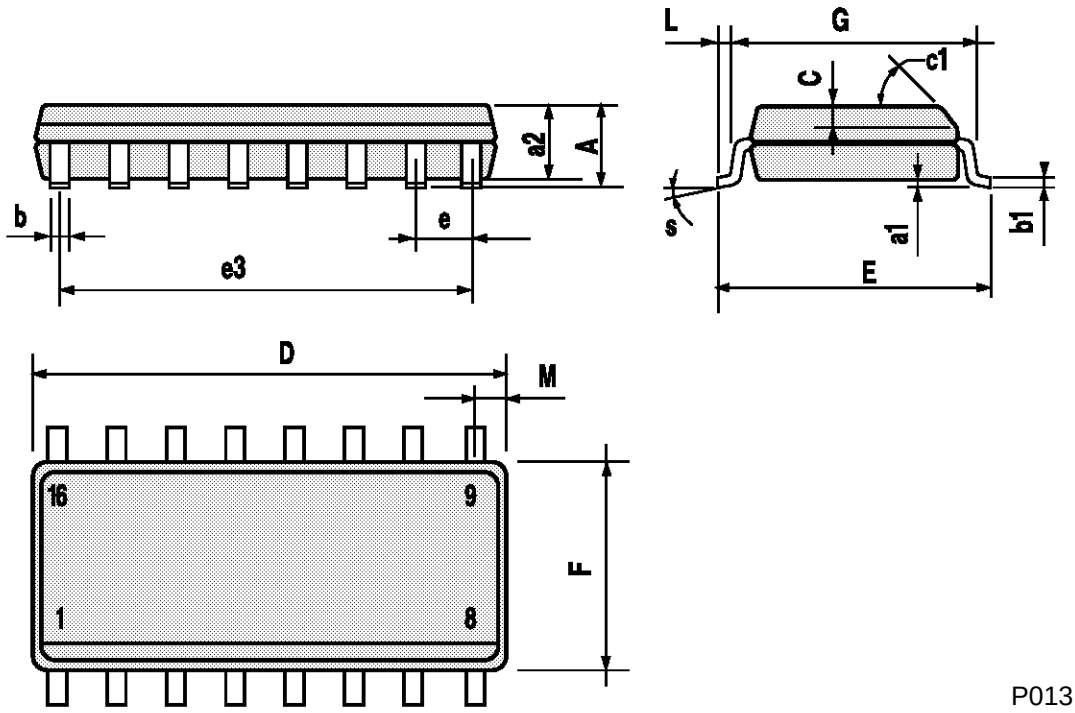
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053D

SO16 (Narrow) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



P013H

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045